

IN THE SPECIFICATION

Please amend the Abstract as follows:

--A solid-state image pickup device for preventing crosstalk between adjacent pixels~~Crosstalk between the adjacent pixels can be prevented by a structure in which by~~
providing an overflow barrier is ~~provided~~ at the deep portion of a substrate. A partial P type region [[150]] is provided at the predetermined position of a lower layer region of the vertical transfer register [[124]] and a channel stop region [[126]]. This P type region ~~150 is used to~~
~~adjust~~adjusts potential in the lower layer region of the vertical transfer register [[124]] and the channel stop region ~~126 so that the potential may become smaller than that of the lower layer~~
~~region of the photosensor 122 in a range from the minimum potential position of the vertical~~
~~transfer register 124 to the overflow barrier 128.~~ Accordingly, since the potential in the lower layer region of the vertical transfer register [[124]] and the channel stop region [[126]] at both sides of the lower layer region is low, electric charges photoelectrically-converted by the sensor region are blocked by this potential barrier and cannot be diffused easily. ~~Thus, crosstalk between the adjacent pixels can be prevented.~~--